



DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
	0.99Ω @ $V_{GS} = 4.5V$	0.45A
20V	1.2Ω @ $V_{GS} = 2.5V$	0.40A
	1.8Ω @ V _{GS} = 1.8V	0.34A
	2.4Ω @ V _{GS} = 1.5V	0.30A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- General Purpose Interfacing Switch
- Power Management Functions
- Analog Switch

Features and Benefits

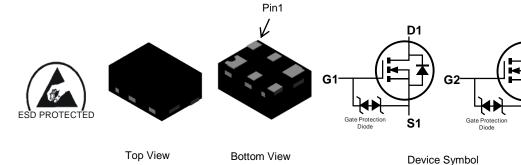
- Low On-Resistance
- Very Low Gate Threshold Voltage, 1.0V Maximum
- Low Input Capacitance
- Fast Switching Speed
- Ultra-Small Surface Mount Package 0.8mm x 0.6mm
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Note 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

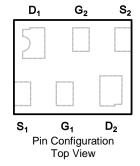
Mechanical Data

- Case: X2-DFN0806-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (e4)

S2

Weight: 0.001 grams (Approximate)





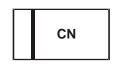
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2991UDA-7B	X2-DFN0806-6	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



Top View

CN = Product Type Marking Code

May 2019

© Diodes Incorporated



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			V_{GSS}	±8	V
Continuous Prain Current (Note 5)	Steady	T _A = +25°C	⊢ I _D	0.45	A
Continuous Drain Current (Note 5)	State	T _A = +70°C		0.36	
Pulsed Drain Current (Note 6)			I _{DM}	1.2	А

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

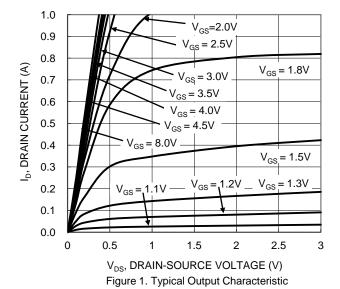
Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		P _D	0.31	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	404	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

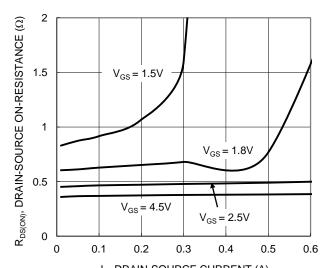
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)								
Drain-Source Breakdown Voltage		BV _{DSS}	20	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current @	T _C = +25°C	I _{DSS}		_	1	μΑ	V _{DS} = 16V, V _{GS} = 0V	
Gate-Source Leakage		I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 5V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)								
Gate Threshold Voltage		$V_{GS(TH)}$	0.4	0.78	1.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
				0.47	0.99	Ω	$V_{GS} = 4.5V, I_D = 100mA$	
Static Drain-Source On-Resistance		Process	_	0.63	1.2		$V_{GS} = 2.5V, I_D = 50mA$	
Static Diam-Source Off-Resistance		R _{DS(ON)}	_	0.84	1.8	12	$V_{GS} = 1.8V, I_D = 20mA$	
			-	1.1	2.4		$V_{GS} = 1.5V, I_D = 10mA$	
Diode Forward Voltage		V_{SD}	-	0.6	1.0	V	$V_{GS} = 0V$, $I_{S} = 10mA$	
DYNAMIC CHARACTERISTICS (Note 8)		•			1	•		
Input Capacitance		Ciss	_	21.5	_	pF	101/1/	
Output Capacitance		Coss	1	4.9		pF	$V_{DS} = 16V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance		C _{rss}		3.7	_	pF	T = 1.0WHZ	
Gate Resistance		R_g	_	0.94	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge		Qg	_	0.35	_	nC	V _{GS} = 4.5V, V _{DS} = 10V,	
Gate-Source Charge		Qgs	1	0.07		nC	I _D = 250mA	
Gate-Drain Charge		Q_{gd}	1	0.08		nC		
Turn-On Delay Time		t _{D(ON)}		5.6	_	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$ $R_{L} = 47\Omega, R_{g} = 10\Omega,$ $I_{D} = 200\text{mA}$	
Turn-On Rise Time		t _R	_	4.9	_	ns		
Turn-Off Delay Time		t _{D(OFF)}	_	60.6	_	ns		
Turn-Off Fall Time		t _F	_	27.6	_	ns		
Reverse Recovery Time		t _{RR}		12.3	1	ns	$I_F = 1.0A$, $di/dt = 100A/\mu s$	
Reverse Recovery Charge		Q_{RR}	_	1.1	_	nC	I _F = 1.0A, di/dt = 100A/μs	

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
 6. Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.
 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to product testing.







I_D, DRAIN-SOURCE CURRENT (A) Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

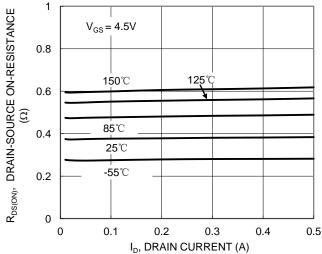
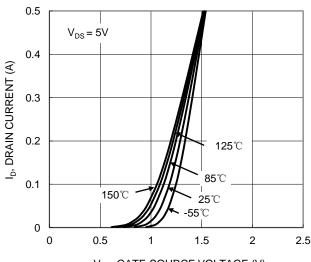


Figure 5. Typical On-Resistance vs. Drain Current and Temperature



V_{GS}, GATE-SOURCE VOLTAGE (V) Figure 2. Typical Transfer Characteristic

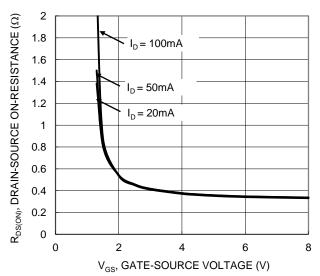


Figure 4. Typical Transfer Characteristic

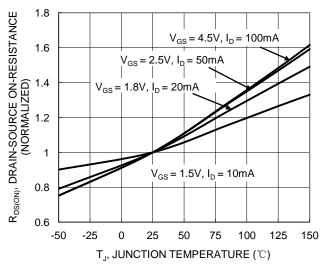


Figure 6. On-Resistance Variation with Temperature



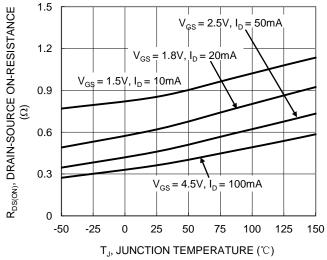


Figure 7. On-Resistance Variation with Temperature

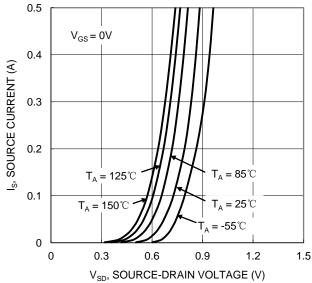


Figure 9. Diode Forward Voltage vs. Current

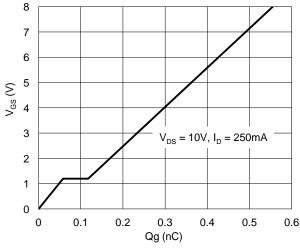


Figure 11. Gate Charge

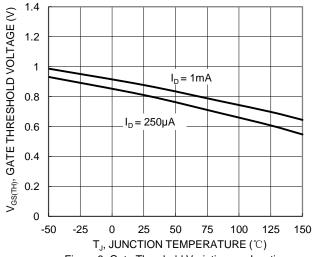


Figure 8. Gate Threshold Variation vs. Junction Temperature

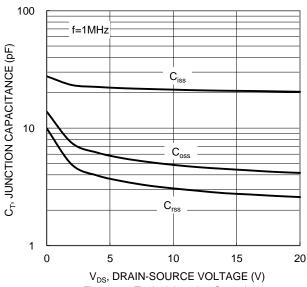


Figure 10. Typical Junction Capacitance

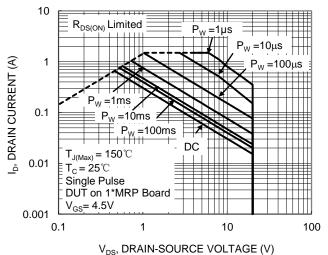


Figure 12. SOA, Safe Operation Area



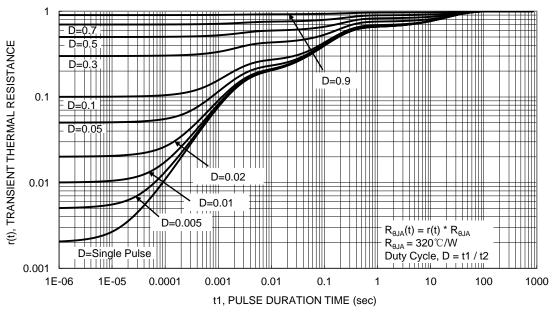


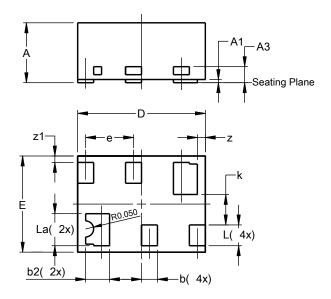
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN0806-6

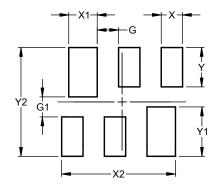


X2-DFN0806-6					
Dim	Min	Max	Тур		
Α		0.40	0.36		
A1	0.00	0.03	0.02		
A3			0.10		
b	0.07	0.15	0.10		
b2	0.10	0.20	0.15		
D	0.75	0.85	0.80		
E	0.55	0.65	0.60		
е			0.30		
k			0.19		
L	0.10	0.18	0.13		
La	0.17	0.25	0.20		
Z			0.05		
z1			0.04		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN0806-6



Dimensions	Value (in mm)			
G	0.150			
G1	0.140			
Х	0.150			
X1	0.200			
X2	0.800			
Υ	0.275			
Y1	0.345			
Y2	0.760			



IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2019, Diodes Incorporated

www.diodes.com

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by Diodes Incorporated manufacturer:

Other Similar products are found below:

614233C 648584F IRFD120 JANTX2N5237 FCA20N60_F109 FDZ595PZ 2SK2545(Q,T) 405094E 423220D TPCC8103,L1Q(CM MIC4420CM-TR VN1206L 614234A 715780A NTNS3166NZT5G SSM6J414TU,LF(T 751625C IPP110N20N3GXK BUK954R8-60E NTE6400 SQJ402EP-T1-GE3 2SK2614(TE16L1,Q) DMN1017UCP3-7 EFC2J004NUZTDG ECH8691-TL-W FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE221 NTE222 NTE2384 NTE2941 NTE2945 NTE2946 NTE2960 NTE2969 NTE2976 NTE6400A NTE2916 NTE2956 NTE2911 DMN2080UCB4-7 TK10A80W,S4X(S STF35N65DM2 STW70N60DM6-4 SSM6P54TU,LF SSM6P69NU,LF DMP22D4UFO-7B DMN1006UCA6-7 DMN16M9UCA6-7